

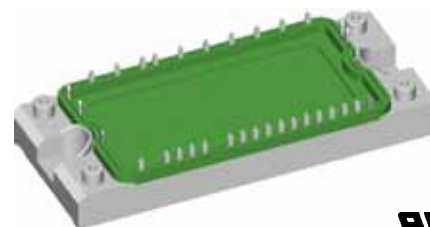
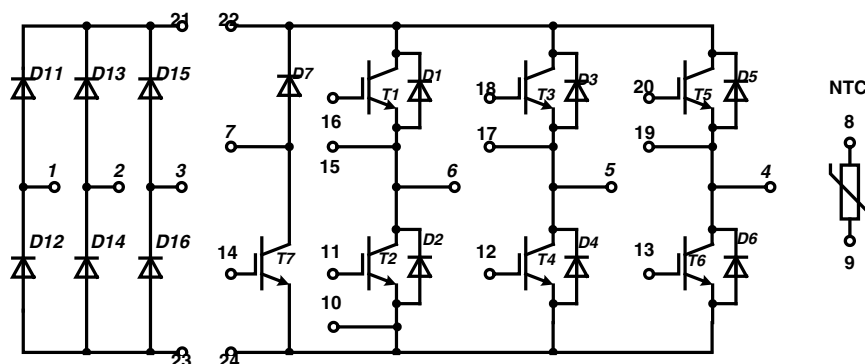
Converter - Brake - Inverter Module XPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAVM} = 105 \text{ A}$	$I_{C25} = 17 \text{ A}$	$I_{C25} = 17 \text{ A}$
$I_{FSM} = 320 \text{ A}$	$V_{CE(sat)} = 1.8 \text{ V}$	$V_{CE(sat)} = 1.8 \text{ V}$

Preliminary data

Part name (Marking on product)

MIXA10WB1200TED




E 72873

Pin configuration see outlines.

Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "E2-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Temperature sense included

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			17		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			12		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			60		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 9\text{ A}; V_{GE} = 15\text{ V}$		1.8 2.1	2.1		V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.3\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.5	6.0	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.01 0.1	0.7		mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500		nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		27			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70			ns
t_r	current rise time			40			ns
$t_{d(off)}$	turn-off delay time			250			ns
t_f	current fall time			100			ns
E_{on}	turn-on energy per pulse			1.1			mJ
E_{off}	turn-off energy per pulse			1.1			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		30		A
SCSOA	short circuit safe operating area						
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
I_{SC}	short circuit current	$R_G = 100\ \Omega;$ non-repetitive		40			A
R_{thJC}	thermal resistance junction to case	(per IGBT)			2.0		K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			19		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			13		A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.85	2.2		V V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -\text{A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	tbd			μC
I_{RM}	max. reverse recovery current			tbd			A
t_{rr}	reverse recovery time			tbd			ns
E_{rec}	reverse recovery energy			tbd			mJ
R_{thJC}	thermal resistance junction to case	(per diode)			2.4		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake T7

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			17		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			12		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			60		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 9\text{ A}; V_{GE} = 15\text{ V}$		1.8 2.1	2.1		V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.3\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5.5	6.0	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.1	0.1	mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500		nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		27			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70			ns
t_r	current rise time			40			ns
$t_{d(off)}$	turn-off delay time			250			ns
t_f	current fall time			100			ns
E_{on}	turn-on energy per pulse			1.1			mJ
E_{off}	turn-off energy per pulse			1.1			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		30		A
SCSOA	short circuit safe operating area						
t_{SC}	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
I_{SC}	short circuit current	$R_G = 100\ \Omega; \text{non-repetitive}$		40			A
R_{thJC}	thermal resistance junction to case	(per IGBT)			2.0		K/W

Brake Chopper D7

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			12		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			8		A
V_F	forward voltage	$I_F = 5\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.95 1.85	2.2		V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.5	0.5		mA mA
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = \text{tbd A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	tbd			μC
I_{RM}	max. reverse recovery current			tbd			A
t_{rr}	reverse recovery time			tbd			ns
E_{rec}	reverse recovery energy			tbd			μJ
R_{thJC}	thermal resistance junction to case	(per diode)			3.4		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D11 - D16

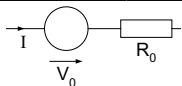
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1600		V
I_{FAV}	average forward current	sine 180°			37		A
I_{DAVM}	max. average DC output current	rect.; $d = 1/3$			105		A
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}$; sine 50 Hz			320		A
					280		A
I^2t	I^2t value for fusing	$t = 10 \text{ ms}$; sine 50 Hz			510		A^2s
					390		A^2s
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			110		W
V_F	forward voltage	$I_F = 50 \text{ A}$					V
				1.34	1.7		V
I_R	reverse current	$V_R = V_{RRM}$			0.02		mA
				0.2			mA
R_{thJC}	thermal resistance junction to case	(per diode)			1.1		K/W

Temperature Sensor NTC

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
R_{25}	resistance	$T_C = 25^{\circ}\text{C}$	4.75	5.0	5.25		k Ω
$B_{25/50}$				3375			K

Module

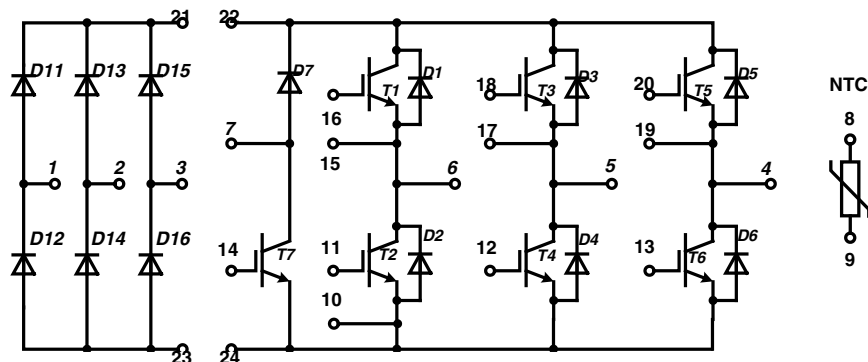
Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
T_{VJ}	operating temperature		-40		125		$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150		$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125		$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}$; 50/60 Hz			2500		V~
CTI	comparative tracking index				-		
M_d	mounting torque (M5)		3		6		Nm
d_S	creep distance on surface		6				mm
d_A	strike distance through air		6				mm
$R_{pin-chip}$	resistance pin to chip			5			m Ω
R_{thCH}	thermal resistance case to heatsink	with heatsink compound		0.02			K/W
Weight				180			g

Equivalent Circuits for Simulation


Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_0	rectifier diode	D8 - D13	$T_{VJ} = 150^{\circ}\text{C}$		0.88		V
R_0					9		m Ω
V_0	IGBT	T1 - T6	$T_{VJ} = 150^{\circ}\text{C}$		1.1		V
R_0					153		m Ω
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 150^{\circ}\text{C}$		1.1		V
R_0					90		m Ω
V_0	IGBT	T7	$T_{VJ} = 150^{\circ}\text{C}$		1.1		V
R_0					153		m Ω
V_0	free wheeling diode	D7	$T_{VJ} = 150^{\circ}\text{C}$		1.15		V
R_0					170		m Ω

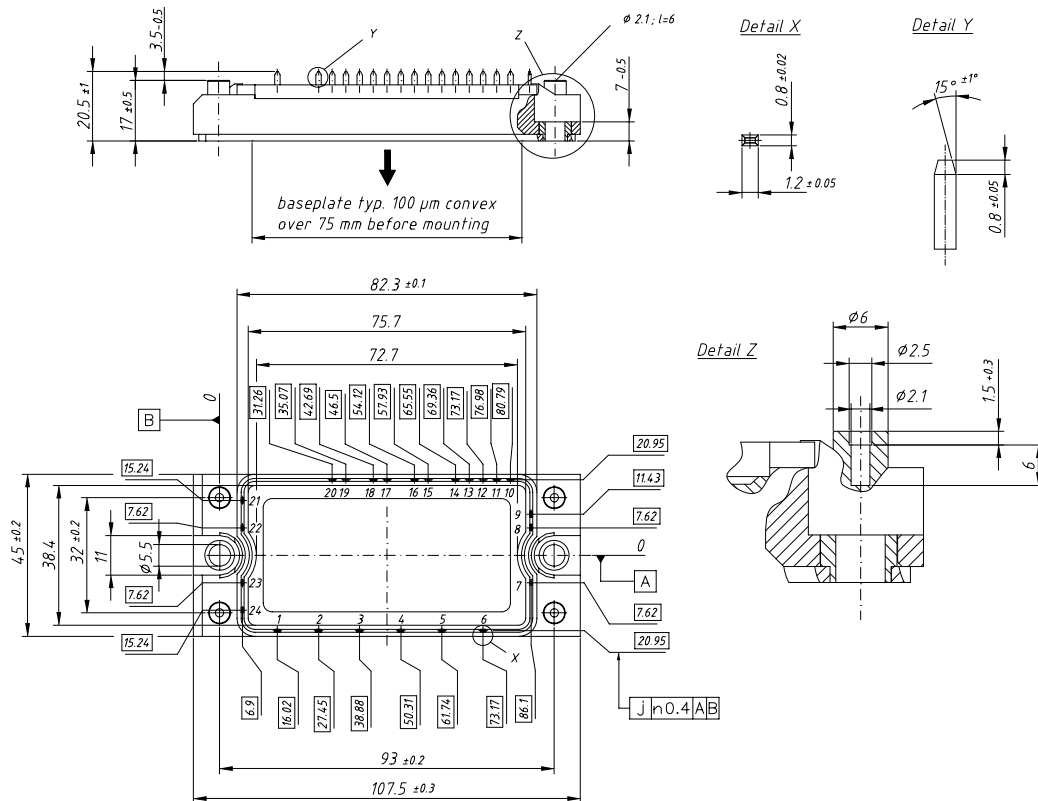
 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Circuit Diagram



Outline Drawing

Dimensions in mm (1 mm = 0.0394")



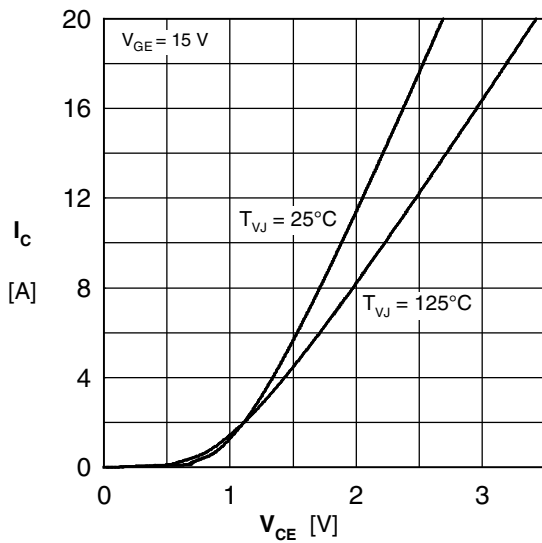


Fig. 1 Typ. output characteristics

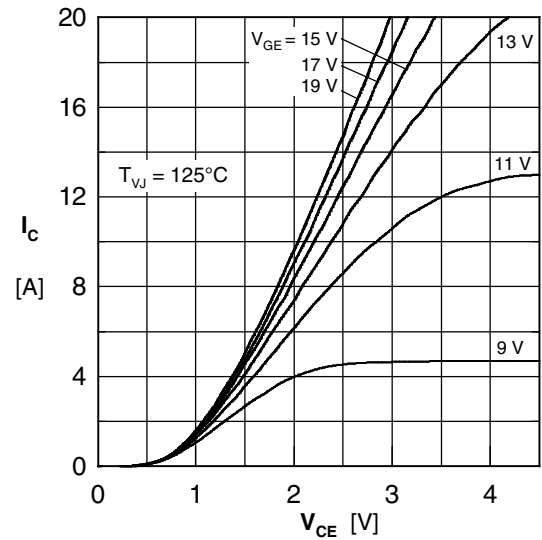


Fig. 2 Typ. output characteristics

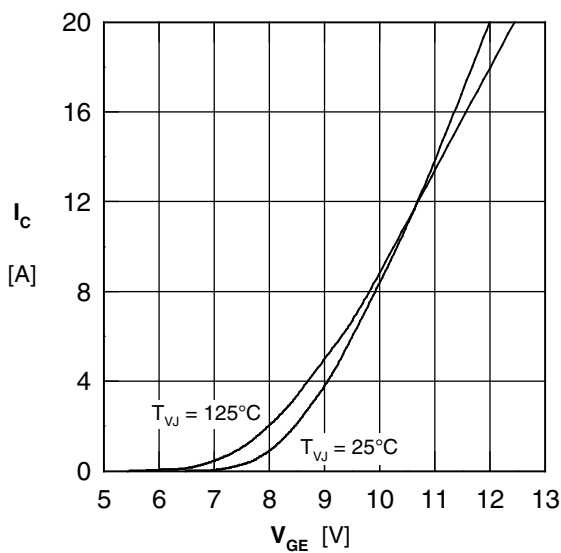


Fig. 3 Typ. transfer characteristics

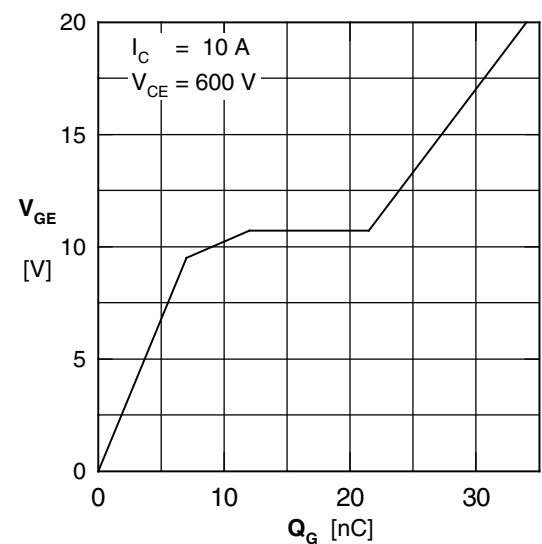


Fig. 4 Typ. turn-on gate charge

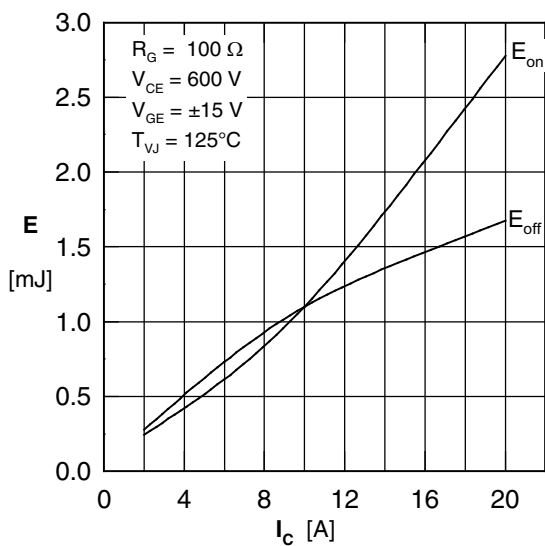


Fig. 5 Typ. switching energy vs. collector current

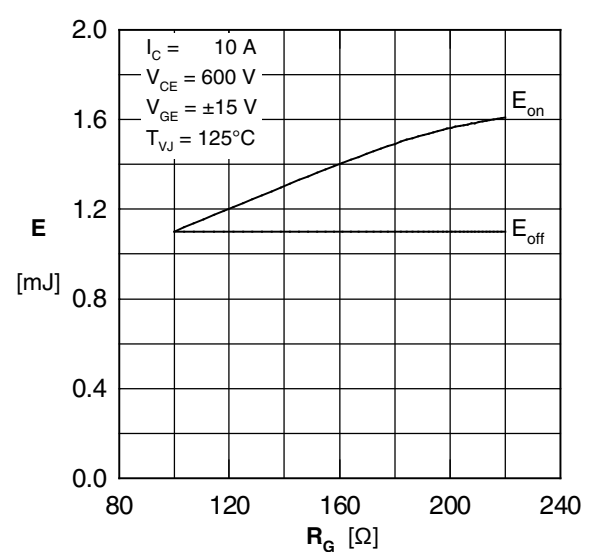


Fig. 6 Typ. switching energy vs. gate resistance

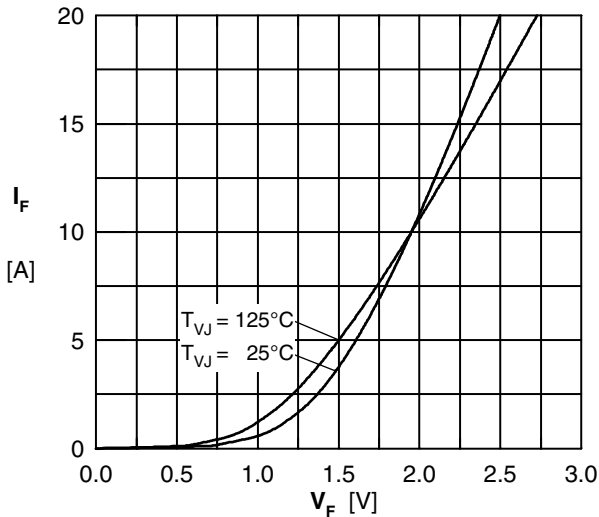


Fig. 7 Typ. forward characteristics

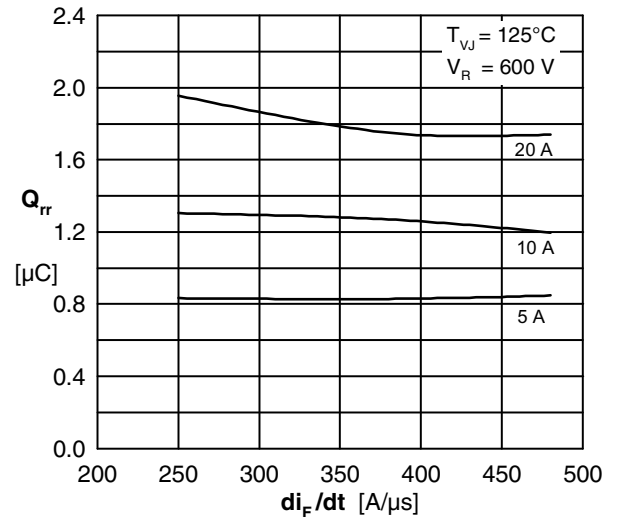


Fig. 8 Typical reverse recovery charge Q_{rr} versus di_F/dt (125°C)

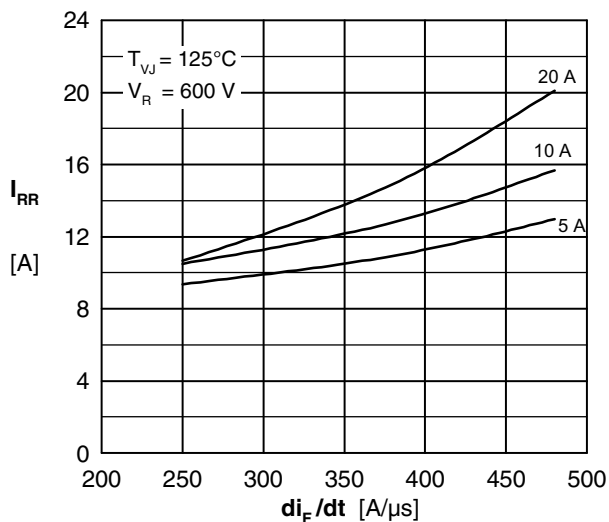


Fig. 9 Typical peak reverse current I_{RR} versus di_F/dt (125°C)

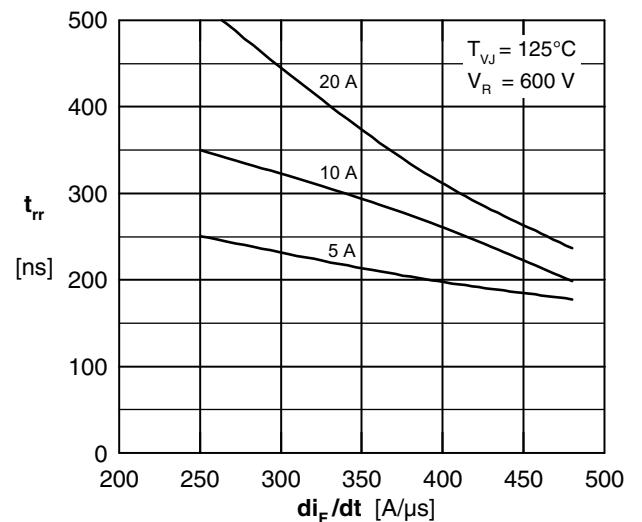


Fig. 10 Typ. recovery time t_{rr} vs. di/dt (125°C)

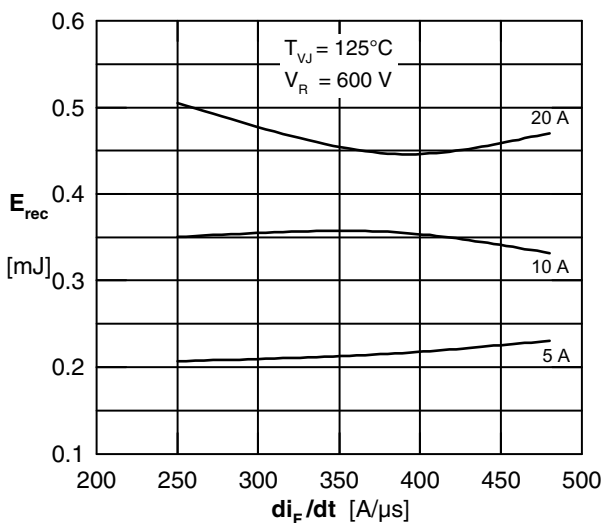


Fig. 11 Typ. recovery energy E_{rec} vs. di_F/dt (125°C)

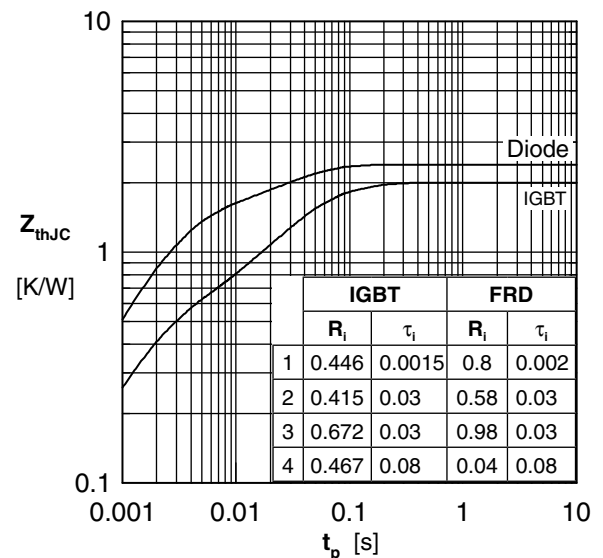


Fig. 8 Transient thermal impedance